

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki, et al. Art Unit : 1765
Serial No. : 09/892,225 Examiner : Mathew J. Song
Filed : June 25, 2001
Title : SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREFOR

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Commissioner for Patents
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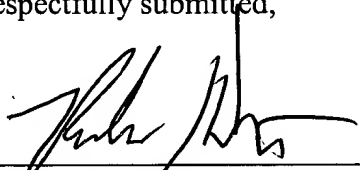
INFORMATION DISCLOSURE STATEMENT

Copies of the references listed on the attached form PTO-1449 are enclosed.

This statement is being filed after a final Office action or a Notice of Allowance, but before payment of the issue fee. A check for \$180 in payment of the late submission fee of §1.17(p) is enclosed. Please apply any other charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 11/22/04



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(Modified)U.S. Department of Commerce
Patent and Trademark OfficeAttorney's Docket No.
07977-279001Application No.
09/892,225**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant
Shunpei Yamazaki, et al.Filing Date
June 25, 2001Group Art Unit
1765**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AJ	JP 04-168769	06/16/1992	Japan			FULL	
	AK							
	AL							
	AM							
	AN							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	AO	Sasaki et al., "A New Low-Temperature Poly-Si TFT Technology Realizing Mobility above 500 cm ² /Vs by Using CW Laser Lateral Crystallization (CLC)", Journal of Institute of Electronics, Information and Communication Engineers, C, Vol. J85-C, No. 8, pp. 601-608, August 2002.
	AP	
	AQ	
	AR	

Examiner Signature

Date Considered

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.